

STATUS OF CLAIMS

Claims 1-27 are pending.

PLEASE AMEND THE CLAIMS AS FOLLOWS:

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D' 4. (TWICE AMENDED) The method of Claim 1 wherein the oxygen containing plasma etchable microelectronics layer is formed from an [an oxygen containing plasma etchable material selected from the group consisting of oxygen containing plasma etchable conductor materials, oxygen containing plasma etchable semiconductor materials, and] oxygen containing plasma etchable dielectric material[s].

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